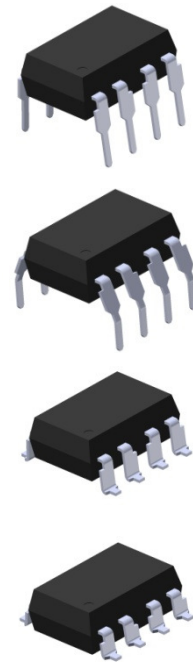


8 PIN DIP DUAL CHANNEL HIGH SPEED 1Mbit/s TRANSISTOR PHOTOCOUPLER

EL253X series

Features

- High speed 1Mbit/s
- High isolation voltage between input and output (Viso=5000 Vrms)
- Guaranteed performance from 0°C to 70°C
- Wide operating temperature range of -40°C to 85°C
- Pb free and RoHS compliant
- UL approved (No. 214129)
- VDE approved (No. 132249)
- SEMKO approved
- NEMKO approved
- DEMKO approved
- FIMKO approved
- CSA approved
- CQC approved

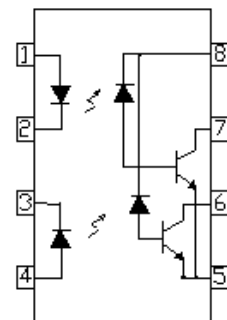


Description

The EL2530 and EL2531 dual channel devices each consist of an infrared emitting diode, optically coupled to a high speed photo detector transistor. A separate connection for the photodiode bias and output-transistor collector increase the speed by several orders of magnitude over conventional phototransistor couplers by reducing the base-collector capacitance of the input transistor.

The devices are packaged in an 8-pin DIP package and available in wide-lead spacing and SMD option.

Schematic



Applications

- Line receivers
- Telecommunication equipments
- Power transistor isolation in motor drives
- Replacement for low speed phototransistor photo couplers
- Feedback loop in switch-mode power supplies
- Home appliances
- High speed logic ground isolation

Pin Configuration

1. Anode
2. Cathode
3. Cathode
4. Anode
5. Gnd
6. Vout2
7. Vout1
8. VCC

8 PIN DIP DUAL CHANNEL HIGH SPEED 1Mbit/s TRANSISTOR PHOTOCOUPLER

EL253X series

Absolute Maximum Ratings ($T_a=25^{\circ}\text{C}$)

Parameter		Symbol	Rating	Unit
Input	Forward current	I_F	25	mA
	Peak forward current (50% duty, 1ms P.W)	I_{FP}	50	mA
	Peak transient current ($\leq 1\mu\text{s}$ P.W, 300pps)	I_{Ftrans}	1	A
	Reverse voltage	V_R	5	V
	Power dissipation	P_{IN}	45	mW
Output	Power dissipation	P_O	35	mW
	Average Output current	$I_{O(AVG)}$	8	mA
	Peak Output current	$I_{O(PK)}$	16	mA
	Output voltage	V_O	-0.5 to 20	V
	Supply voltage	V_{CC}	-0.5 to 30	V
Isolation voltage ^{*1}		V_{ISO}	5000	V rms
Operating temperature		T_{OPR}	-40 ~ +100	$^{\circ}\text{C}$
Storage temperature		T_{STG}	-40 ~ +125	$^{\circ}\text{C}$
Soldering temperature ^{*2}		T_{SOL}	260	$^{\circ}\text{C}$

Notes

*1 AC for 1 minute, R.H.= 40 ~ 60% R.H. In this test, pins 1, 2, 3, 4 are shorted together, and pins 5, 6, 7, 8 are shorted together.

*2 For 10 seconds.

8 PIN DIP DUAL CHANNEL HIGH SPEED 1Mbit/s TRANSISTOR PHOTOCOUPLER

EL253X series

Electrical Characteristics ($T_A=0$ to 70°C unless specified otherwise)

Input

Parameter	Symbol	Min.	Typ.*	Max.	Unit	Conditions
Forward voltage	V_F	-	1.45	1.8	V	$I_F = 16\text{mA}$, $T_A=25^\circ\text{C}$
Reverse Voltage	V_R	5.0	-	-	V	$I_R = 10\mu\text{A}$
Temperature coefficient of forward voltage	V_F/T_A	-	-1.9	-	mV/ $^\circ\text{C}$	$I_F=16\text{mA}$
Input Capacitance	C_{IN}	-	60	-	pF	$V_F=0\text{V}$, $f=1\text{MHz}$

Output

Parameter	Symbol	Min.	Typ.*	Max.	Unit	Conditions
Logic High Output Current	I_{OH}	-	0.001	0.5	μA	$I_F=0\text{mA}$, $V_O=V_{CC}=5.5\text{V}$, $T_A=25^\circ\text{C}$
		-	-	50		$I_F=0\text{mA}$, $V_O=V_{CC}=15\text{V}$, $T_A=25^\circ\text{C}$
Logic Low Supply Current	I_{CCL}	-	140	400	μA	$I_{F1}=I_{F2}=16\text{mA}$, $V_O=\text{Open}$, $V_{CC}=15\text{V}$
Logic High Supply Current	I_{CCH}	-	0.01	1	μA	$I_F=0\text{mA}$, $V_O=\text{Open}$, $V_{CC}=15\text{V}$, $T_A=25^\circ\text{C}$
		-	-	4		$I_F=0\text{mA}$, $V_O=\text{Open}$, $V_{CC}=15\text{V}$

* Typical values at $T_A = 25^\circ\text{C}$

8 PIN DIP DUAL CHANNEL HIGH SPEED 1Mbit/s TRANSISTOR PHOTOCOUPLER

EL253X series

Transfer Characteristics ($T_A=0$ to 70°C unless specified otherwise)

Parameter		Symbol	Min.	Typ.*	Max.	Unit	Conditions
Current Transfer Ratio	EL2530	CTR	7	-	50	%	$I_F = 16\text{mA}$, $V_O = 0.4\text{V}$, $V_{CC}=4.5\text{V}$, $T_A=25^\circ\text{C}$
	EL2531		19	-	50		
	EL2530		5	-	-		$I_F = 16\text{mA}$, $V_O = 0.5\text{V}$, $V_{CC}=4.5\text{V}$
	EL2531		15	-	-		
Logic Low Output Voltage	EL2530	V_{OL}	-	0.18	0.5	V	$I_F = 16\text{mA}$, $I_O = 1.1\text{mA}$, $V_{CC}=4.5\text{V}$, $T_A=25^\circ\text{C}$
	EL2531		-	0.25	0.5		$I_F = 16\text{mA}$, $I_O = 3\text{mA}$, $V_{CC}=4.5\text{V}$, $T_A=25^\circ\text{C}$
	EL2530		-	-	0.5		$I_F = 16\text{mA}$, $I_O = 0.8\text{mA}$, $V_{CC}=4.5\text{V}$
	EL2531		-	-	0.5		$I_F=16\text{mA}$, $I_O=2.4\text{mA}$, $V_{CC}=4.5\text{V}$

Switching Characteristics ($T_A=0$ to 70°C unless specified otherwise, $I_F=16\text{mA}$, $V_{CC}=5\text{V}$)

Parameter		Symbol	Min.	Typ.*	Max.	Unit	Conditions
Propagation Delay Time to Logic Low (Fig.8)	EL2530	t _{PHL}	-	0.35	1.5	μs	R _L =4.1KΩ, T _A =25℃
			-	-	2.0		R _L =4.1KΩ
	EL2531		-	0.35	0.8		R _L =1.9KΩ, T _A =25℃
			-	-	1.0		R _L =1.9KΩ
Propagation Delay Time to Logic High (Fig.8)	EL2530	t _{PLH}	-	0.5	1.5	μs	R _L =4.1KΩ, T _A =25℃
			-	-	2.0		R _L =4.1KΩ
	EL2531		-	0.3	0.8		R _L =1.9KΩ, T _A =25℃
			-	-	1.0		R _L =1.9KΩ
Common Mode Transient Immunity at Logic High (Fig.9) ^{*3}	EL2530	CM _H	1,000	10,000	-	V/μs	I _F = 0mA , V _{CM} =10Vp-p, R _L =4.1KΩ, T _A =25℃
	EL2531		1,000	10,000	-		I _F = 0mA , V _{CM} =1000Vp-p, R _L =1.9KΩ, T _A =25℃
Common Mode Transient Immunity at Logic Low (Fig.9) ^{*3}	EL2530	CM _L	1,000	10,000	-	V/μs	I _F = 16mA , V _{CM} =10Vp-p, R _L =4.1KΩ, T _A =25℃
	EL2531		1,000	10,000	-		I _F = 16mA , V _{CM} =1000Vp-p, R _L =1.9KΩ, T _A =25℃

* Typical values at $T_A = 25^\circ\text{C}$

8 PIN DIP DUAL CHANNEL HIGH SPEED 1Mbit/s TRANSISTOR PHOTOCOUPLER

EL253X series

Typical Performance Curves

Fig.1 Forward Current vs. Forward Voltage

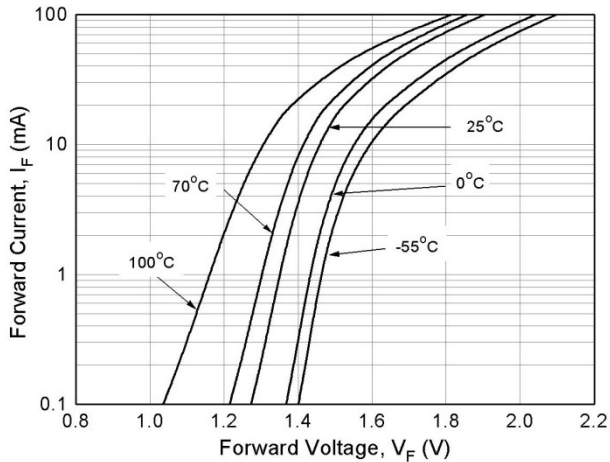


Fig.2 Normalized Current Transfer Ratio vs. Forward Current

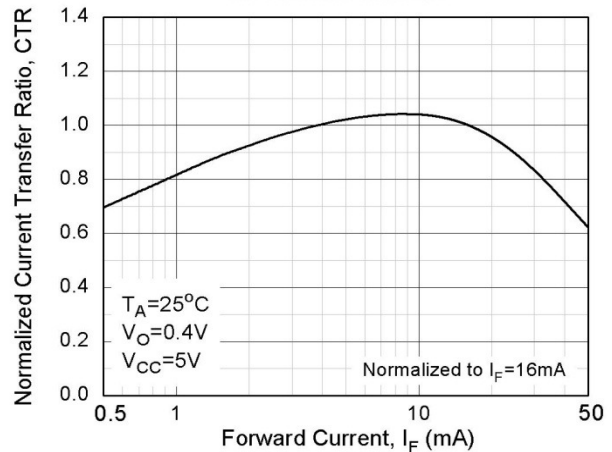


Fig.3 Normalized Current Transfer Ratio vs. Ambient Temperature

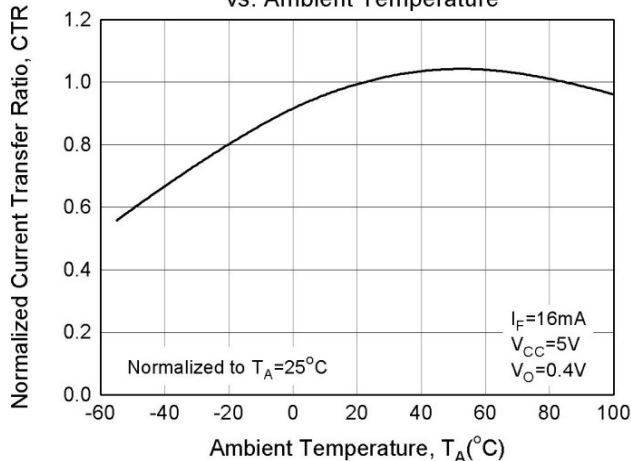


Fig.4 Output Current vs Output Voltage

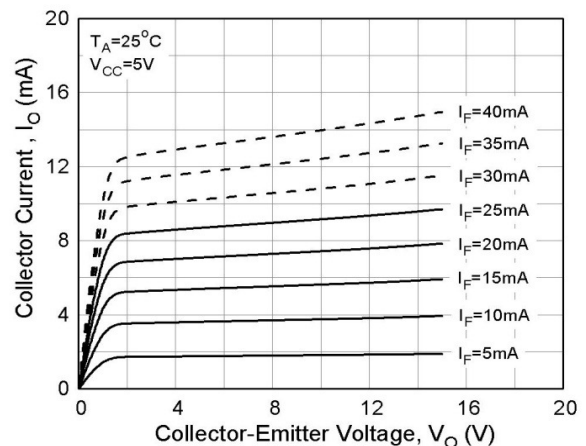


Fig.5 Logic High Output Current vs. Temperature

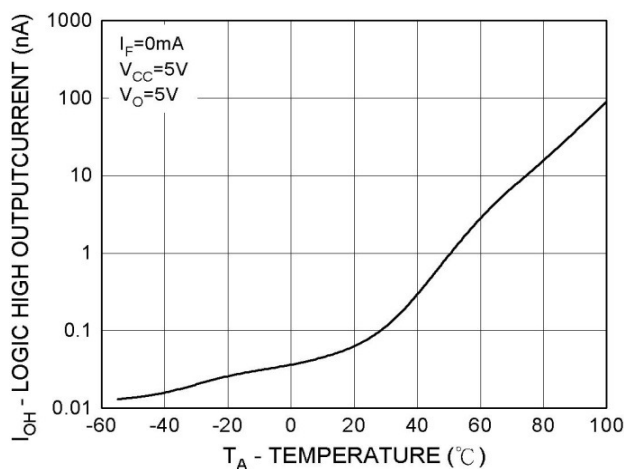
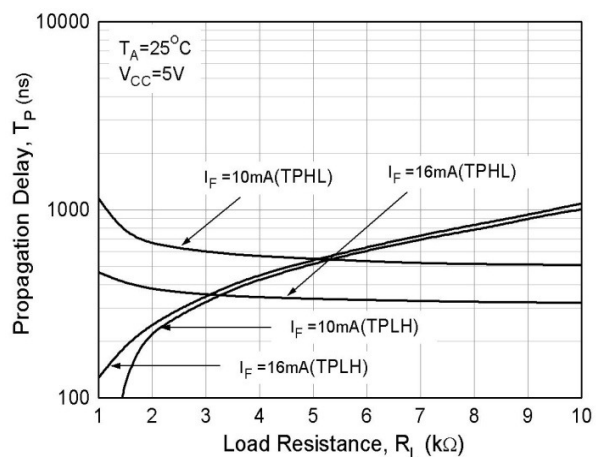


Fig.6 Propagation Delay vs. Load Resistance



8 PIN DIP DUAL CHANNEL HIGH SPEED 1Mbit/s TRANSISTOR PHOTOCOUPLER

EL253X series

Fig.7 Propagation Delay vs. Temperature

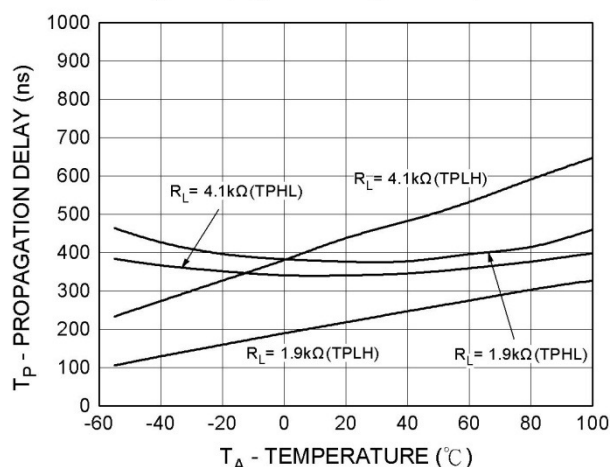


Figure 8 Switching Time Test Circuit & Waveform

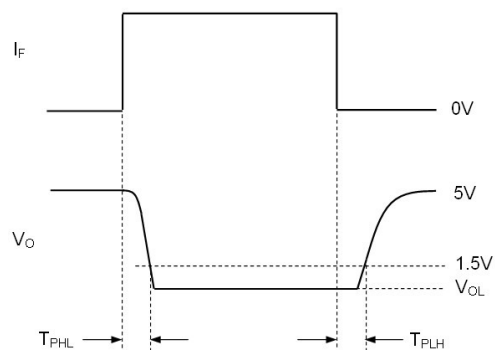
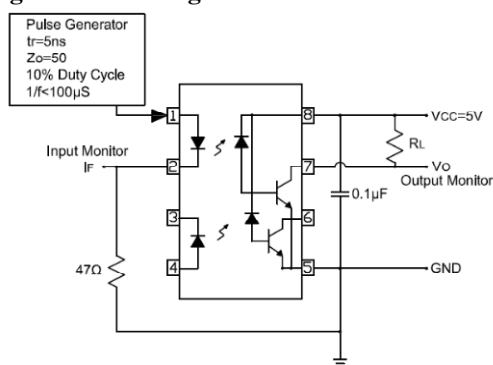
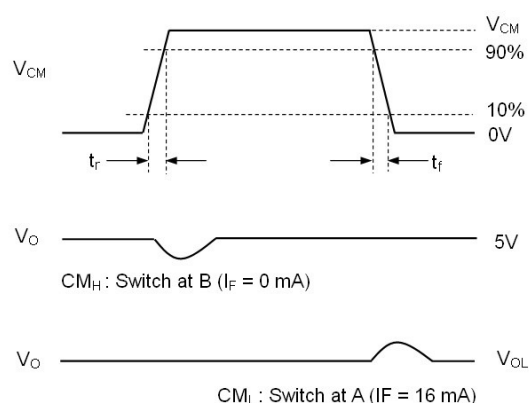
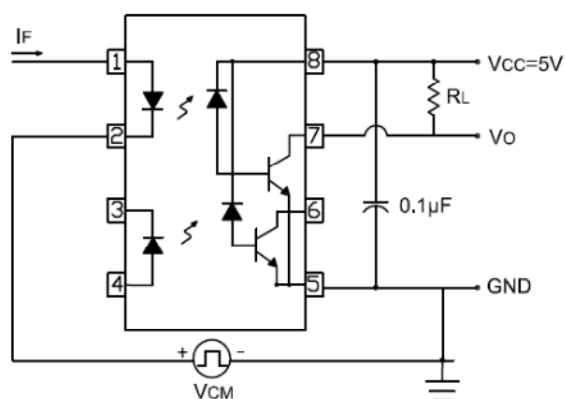


Figure 9 Transient Immunity Test Circuit & Waveform



Note:

- *3 Common mode transient immunity in logic high level is the maximum tolerable (positive) dV_{CM}/dt on the leading edge of the common mode pulse signal V_{CM} , to assure that the output will remain in a logic high state (i.e., $V_O > 2.0V$).
- Common mode transient immunity in logic low level is the maximum tolerable (negative) dV_{CM}/dt on the trailing edge of the common mode pulse signal, V_{CM} , to assure that the output will remain in a logic low state (i.e., $V_O < 0.8V$).

**8 PIN DIP DUAL CHANNEL HIGH SPEED
1Mbit/s TRANSISTOR PHOTOCOUPLER****EL253X series**

Order Information**Part Number****EL253XY(Z)-V****Note**

- X = Part no. (0 or 1)
Y = Lead form option (S, S1, M or none)
Z = Tape and reel option (TA, TB or none)
V = VDE (optional)

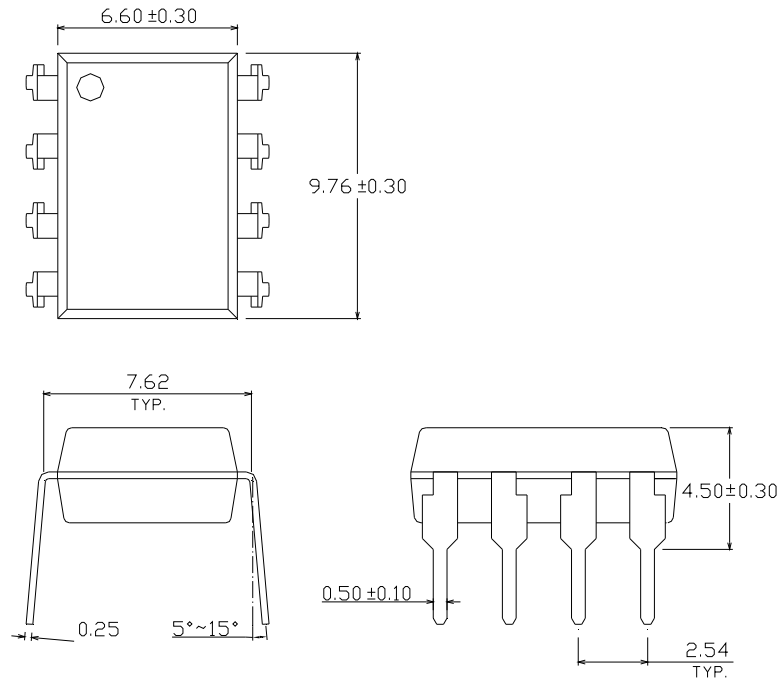
Option	Description	Packing quantity
None	Standard DIP-8	45 units per tube
M	Wide lead bend (0.4 inch spacing)	45 units per tube
S (TA)	Surface mount lead form + TA tape & reel option	1000 units per reel
S (TB)	Surface mount lead form + TB tape & reel option	1000 units per reel
S1 (TA)	Surface mount lead form (low profile) + TA tape & reel option	1000 units per reel
S1 (TB)	Surface mount lead form (low profile) + TB tape & reel option	1000 units per reel

8 PIN DIP DUAL CHANNEL HIGH SPEED 1Mbit/s TRANSISTOR PHOTOCOUPLER

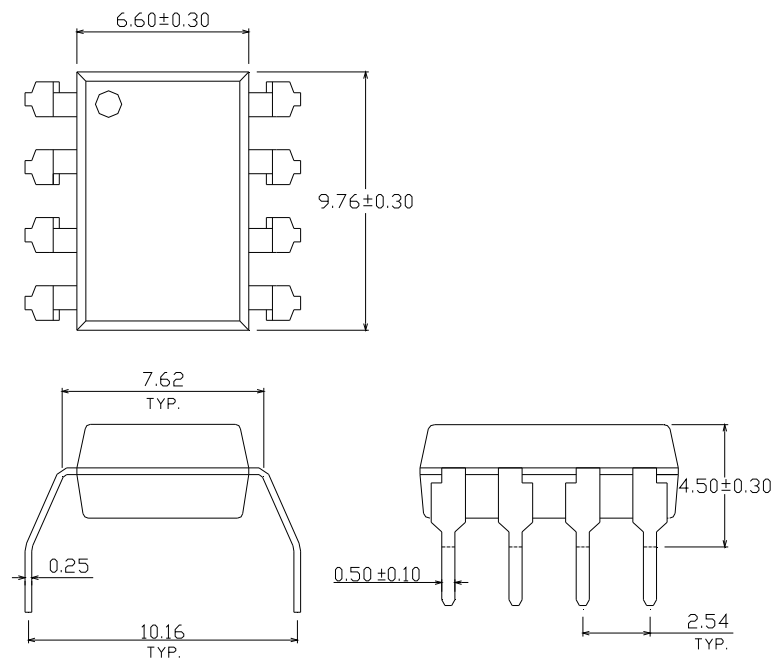
EL253X series

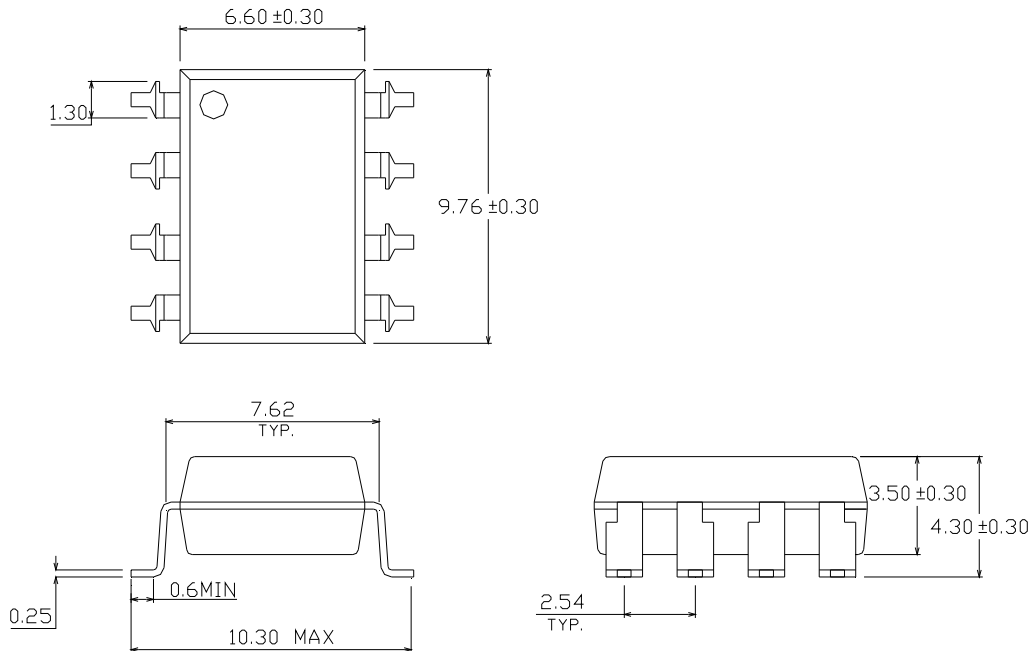
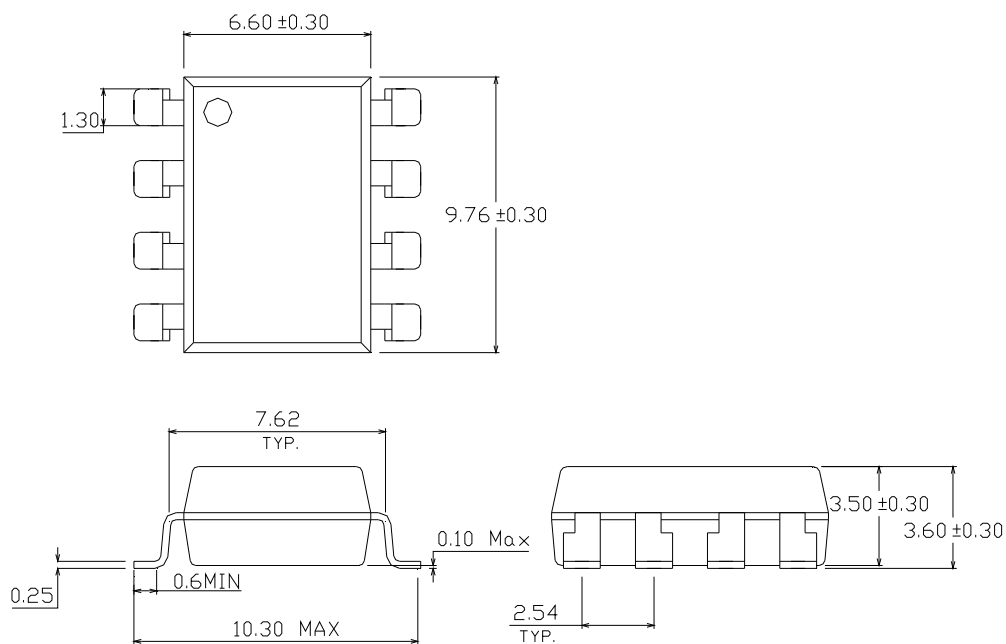
Package Drawing (Dimensions in mm)

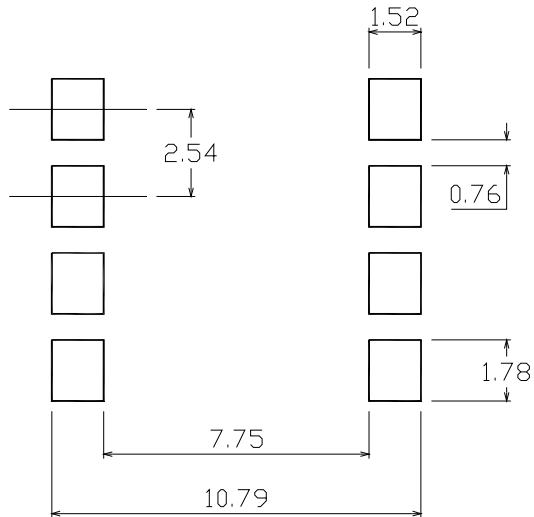
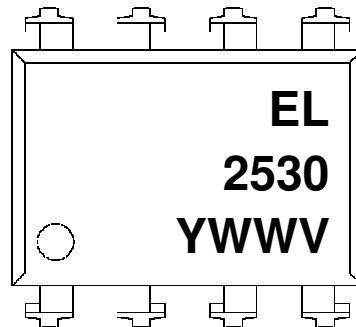
Standard DIP Type



Option M Type



**8 PIN DIP DUAL CHANNEL HIGH SPEED
1Mbit/s TRANSISTOR PHOTOCOUPLER****EL253X series****Option S Type****Option S1 Type**

**8 PIN DIP DUAL CHANNEL HIGH SPEED
1Mbit/s TRANSISTOR PHOTOCOUPLER****EL253X series****Recommended pad layout for surface mount leadform****Device Marking****Notes**

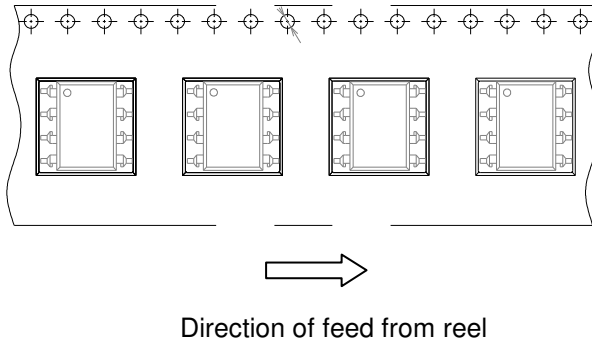
- 2530 denotes Device Number
- Y denotes 1 digit Year code
- WW denotes 2 digit Week code
- V denotes VDE (optional)

8 PIN DIP DUAL CHANNEL HIGH SPEED 1Mbit/s TRANSISTOR PHOTOCOUPLER

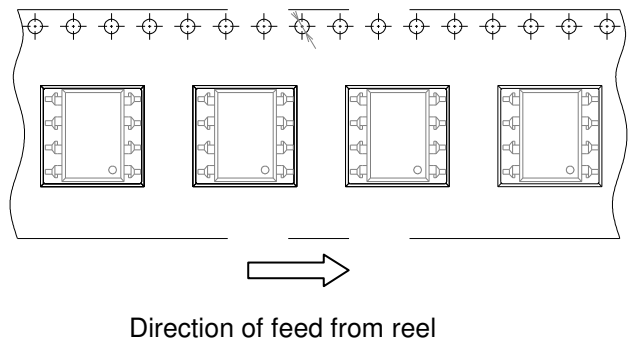
EL253X series

Tape & Reel Packing Specifications

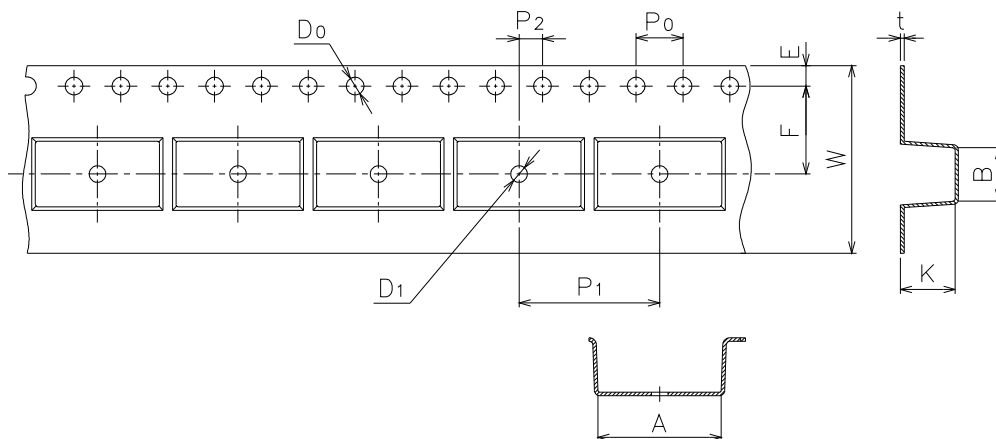
Option TA



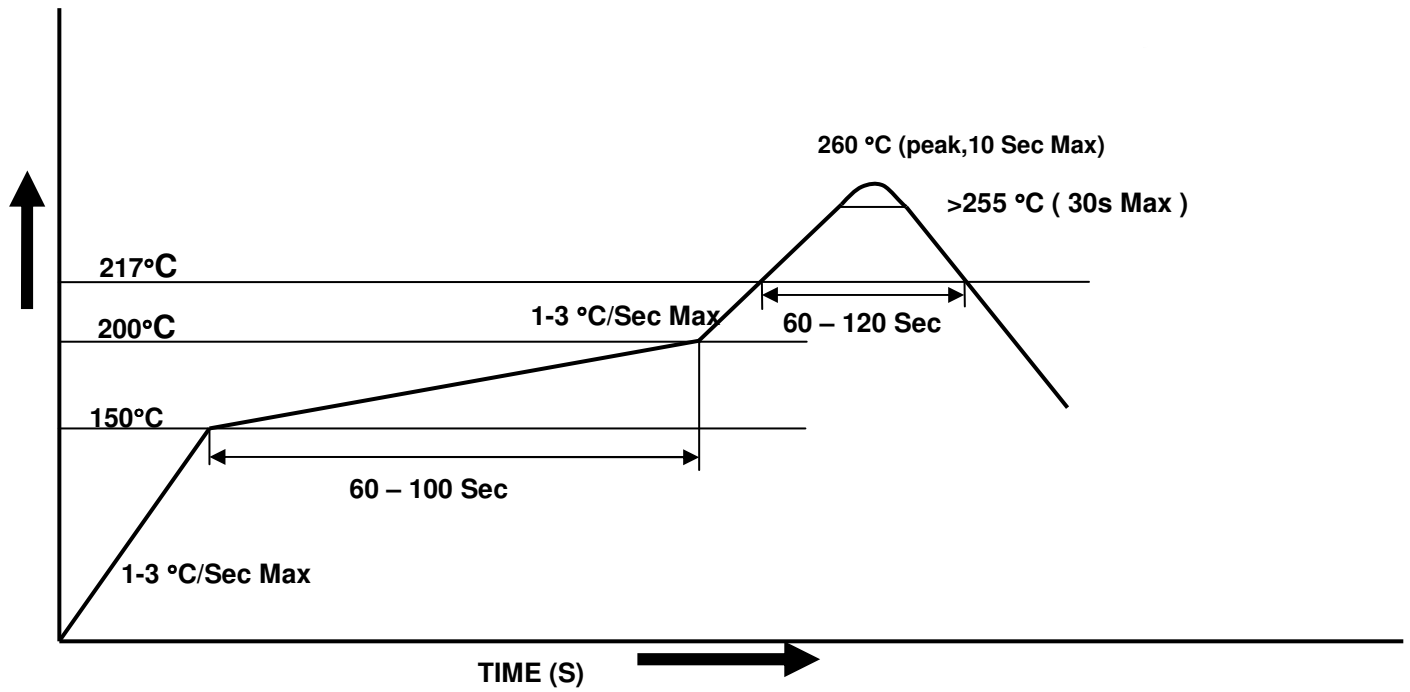
Option TB



Tape dimensions



Dimension No.	A	B	Do	D1	E	F
Dimension(mm)	10.4±0.1	10.0±0.1	1.5±0.1	1.5±0.1	1.75±0.1	7.5±0.1
Dimension No.	Po	P1	P2	t	W	K
Dimension(mm)	4.0±0.1	12.0±0.1	2.0±0.1	0.4±0.1	16.0+0.3/ -0.1	4.5±0.1

**8 PIN DIP DUAL CHANNEL HIGH SPEED
1Mbit/s TRANSISTOR PHOTOCOUPLER****EL253X series****Solder Reflow Temperature Profile**

**8 PIN DIP DUAL CHANNEL HIGH SPEED
1Mbit/s TRANSISTOR PHOTOCOUPLER****EL253X series**

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